

Silicon NPN Power Transistors

2SC2611

DESCRIPTION

- With TO-126 package
- High breakdown voltage

APPLICATIONS

- For high voltage amplifier TV video output applications

PINNING

| PIN | DESCRIPTION |
|-----|--------------------------------------|
| 1 | Emitter |
| 2 | Collector;connected to mounting base |
| 3 | Base |

ABSOLUTE MAXIMUM RATINGS($T_c=25^\circ\text{C}$)

| SYMBOL | PARAMETER | CONDITIONS | VALUE | UNIT |
|-----------|-----------------------------|------------------------|---------|------------------|
| V_{CBO} | Collector-base voltage | Open emitter | 300 | V |
| V_{CEO} | Collector-emitter voltage | Open base | 300 | V |
| V_{EBO} | Emitter-base voltage | Open collector | 5 | V |
| I_C | Collector current | | 0.1 | A |
| P_C | Collector power dissipation | $T_a=25^\circ\text{C}$ | 1.25 | W |
| T_j | Junction temperature | | 150 | $^\circ\text{C}$ |
| T_{stg} | Storage temperature | | -55~150 | $^\circ\text{C}$ |

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT |
|----------------------|--------------------------------------|---|-----|------|-----|------|
| V _{(BR)CEO} | Collector-emitter breakdown voltage | I _C =1mA; R _{BE} =∞ | 300 | | | V |
| V _{(BR)CBO} | Collector-base breakdown voltage | I _C =10μA; I _E =0 | 300 | | | V |
| V _{(BR)EBO} | Emitter-base breakdown voltage | I _E =10μA; I _C =0 | 5 | | | V |
| V _{CE(sat)} | Collector-emitter saturation voltage | I _C =20mA; I _B =2mA | | | 1.5 | V |
| I _{CEO} | Collector cut-off current | V _{CE} =250V; R _{BE} =∞ | | | 1.0 | μA |
| h _{FE} | DC current gain | I _C =20mA; V _{CE} =20V | 30 | | 200 | |
| f _T | Transition frequency | I _C =20mA; V _{CE} =20V | 50 | 80 | | MHz |
| C _{OB} | Collector output capacitance | I _E =0; V _{CB} =20V; f=1MHz | | | 4.0 | pF |

PACKAGE OUTLINE

